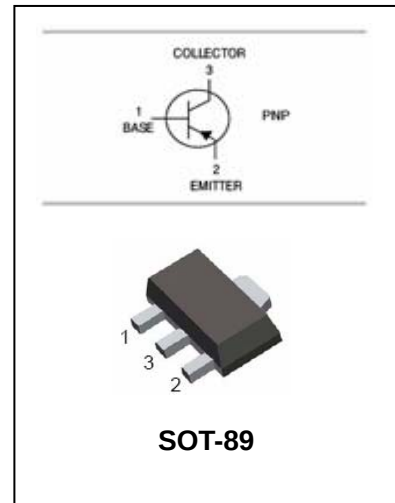


PNP Silicon Epitaxial Planar Transistor

KTA1273

FEATURES

- 1W(Mounted on Ceramic Substrate).
- Small flat package.
- Complementary: KTC3205.



ORDERING INFORMATION

Type No.	Marking	Package Code
KTA1273	1273	SOT-89

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-2	A
I_E	Emitter Current	2	A
P_C	Collector Dissipation	1	W
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	°C



PNP Silicon Epitaxial Planar Transistor

KTA1273

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1mA, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -30V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -2V, I_C = -500mA$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1.5A, I_B = -0.03A$			-2.0	V
Base-emitter voltage	V_{BE}	$V_{CE} = -2V, I_C = -500mA$			-1.0	V
Transition frequency	f_T	$V_{CE} = -2V, I_C = -500mA$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		48		pF

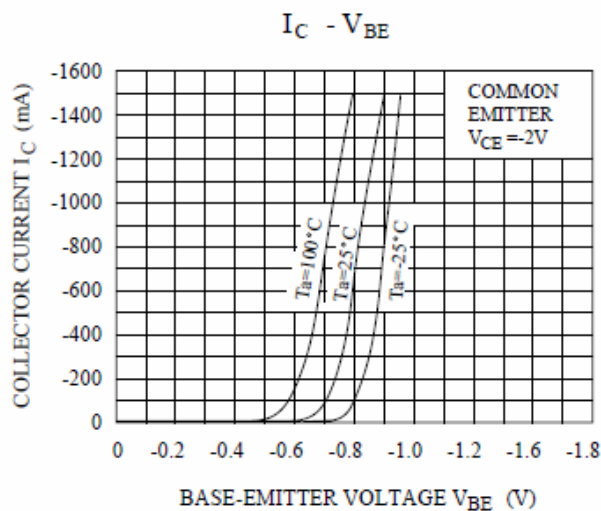
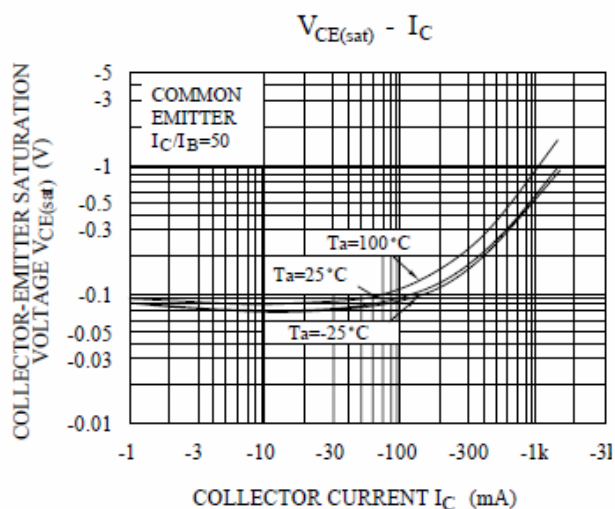
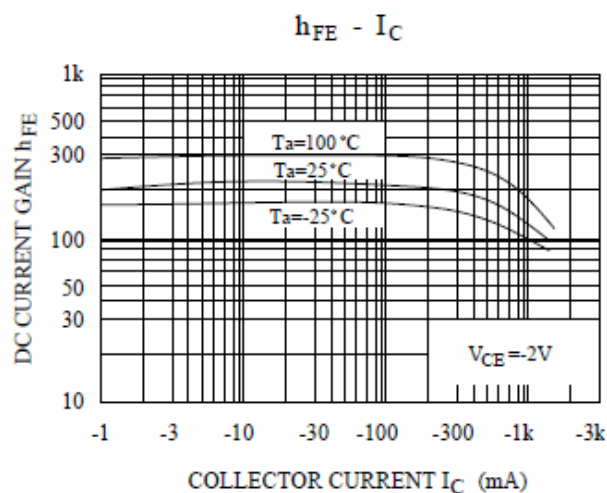
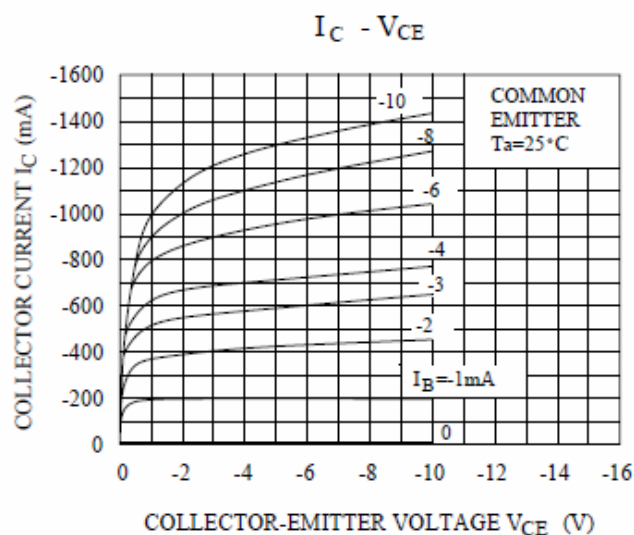
CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320

PNP Silicon Epitaxial Planar Transistor

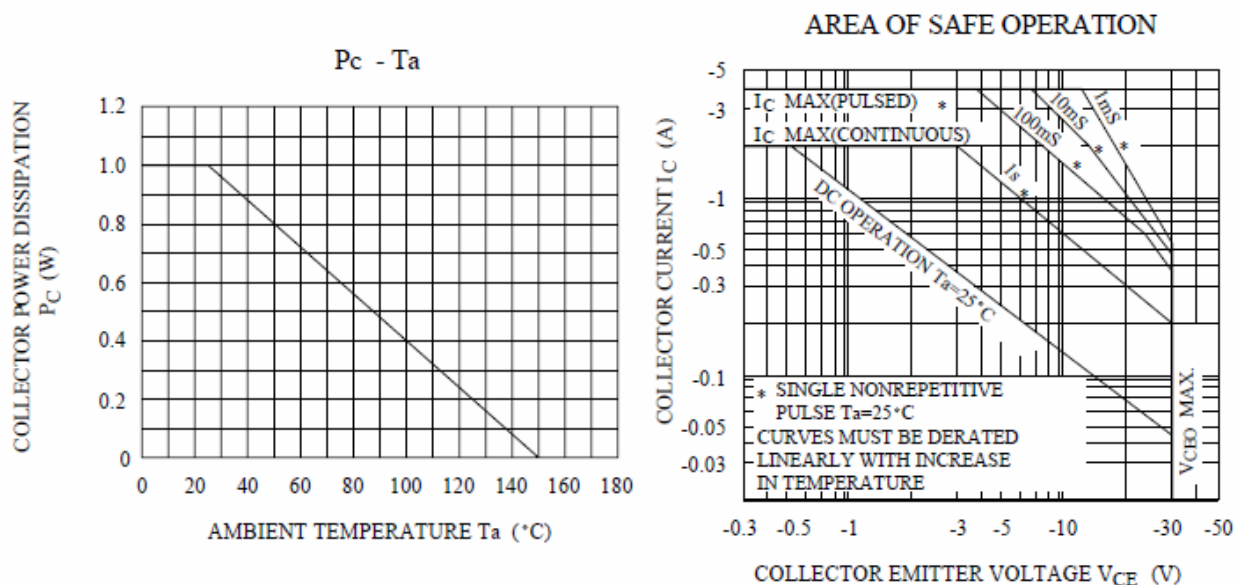
KTA1273

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



PNP Silicon Epitaxial Planar Transistor

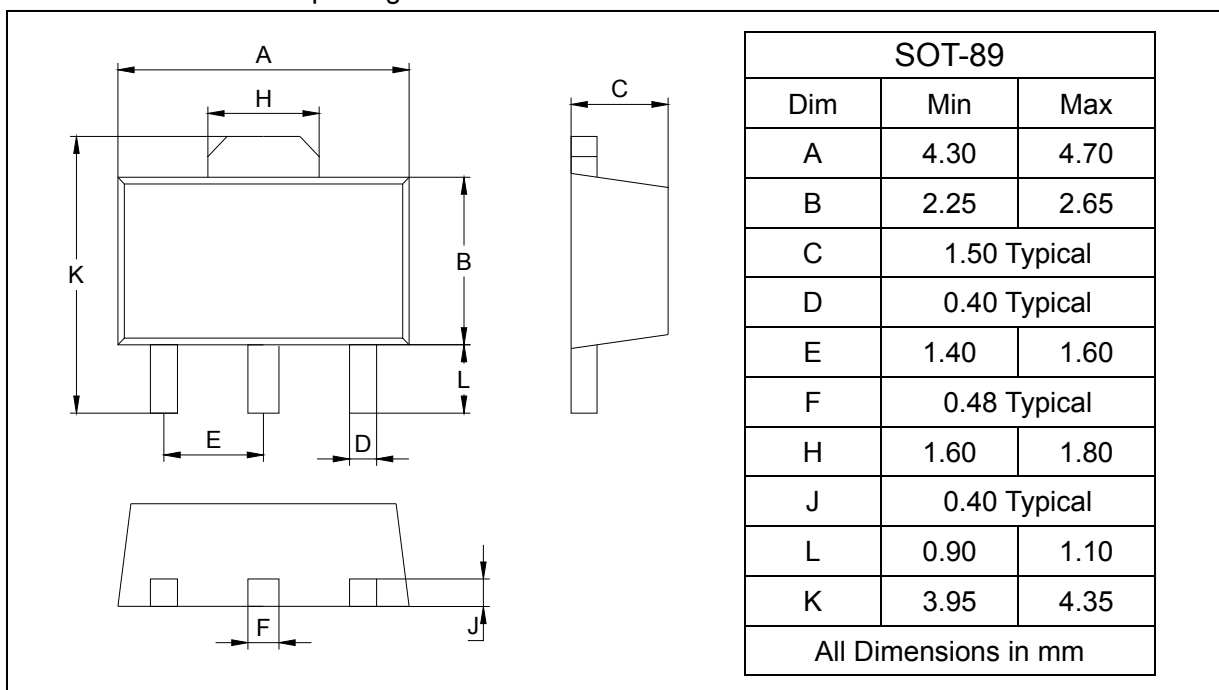
KTA1273



PACKAGE OUTLINE

Plastic surface mounted package

SOT-89

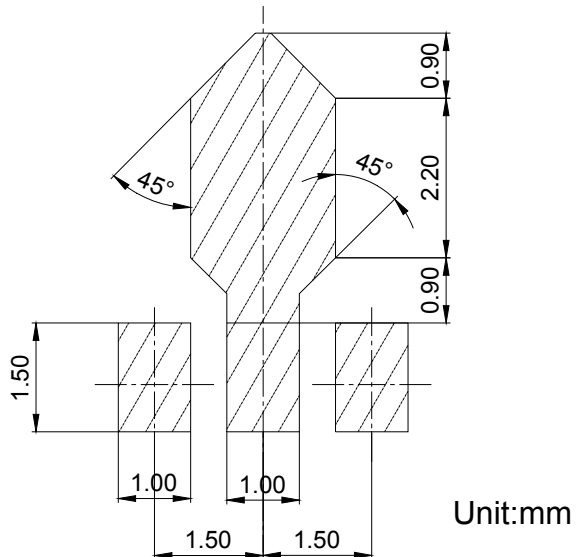




PNP Silicon Epitaxial Planar Transistor

KTA1273

SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
KTA1273	SOT-89	1000/Tape&Reel